

an active layer including a polycrystalline silicon film where a drain, a source and a channel are defined, grain sizes of the drain and source being greater than a grain size of the channel; and

5 a gate formed from a refractory metal.

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8. (Twice Amended) A thin film transistor comprising:

an insulator substrate;

a refractory metal gate electrode located on the insulator substrate;

an insulator film provided on the insulator substrate and the gate electrode; and

5 a polycrystalline silicon film located on the insulator film, a channel defined in a first portion of the polycrystalline silicon film over the gate electrode, a drain and a source defined in second and third portions of the polycrystalline silicon film over the insulator substrate, grain sizes of the drain and source being greater than a grain size of the channel.

9. (Twice Amended) The thin film transistor according to claim 8, wherein the grain size of the channel is at least about 500 Å to provide a desired on current of the thin film transistor.